How the process works:
- Allow the slurry to harden.
- How you make things
to design you need to know about
- Process variables?

How do we measure accuracy?

HW1

Office hours to 1:30 9/12
Section poll
94% Ht etal at 51o2: 2 minutes Strip PR

Deep Reactive Ion Etch (SCS 501)

Head bake

Develop PR

Expose with mask (RED)

Spin cast photo resist

Start w/ 20mm/4mm 50I water

Lots of resist lines

Commercial AR process

Vapor

Nahoko first features

25mm/w

Lens 4 - 10x reduction

Mask

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Glass substrate/wafer → Photo resist

Glass w/ opaque layer

Place

Lenses

154th 3.16

Lithography - 4 writing in stone or site
SCS SOT layer

Stamps the PL pattern into the film. Place IS like a cookie cutter

For curing: PLATE IS like a cookie cutter

Diet

- Moisture Film
- Spent OS
- Spray OS
- Other ways to put down PL

Additional Film

- A meets function of the film, the film is uniform. Film is uniform.

- Other function of the film, the film is uniform. Film is uniform.

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HF - doesn't etch SCS at all) selective!
- etches SiO$_2$ @ 1mm/minute
- isotropic - same etch rate in every direction

Cross Section

Cross Section

Original SiO$_2$ surface

Top view/layer view, 10um square

10um square w/ 2mm hole